PROCESS CP331

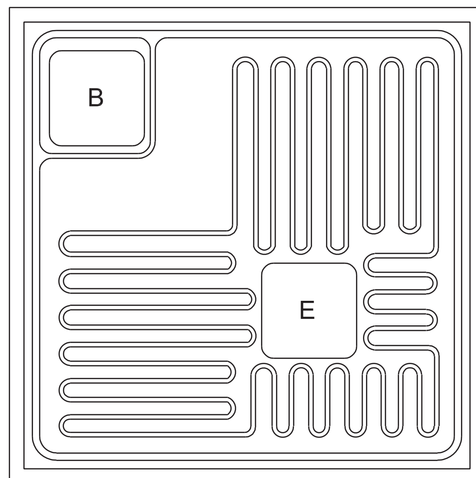
Power Transistor

NPN - High Voltage Darlington Transistor Chip

PROCESS DETAILS

Die Size	39.4 x 39.4 MILS
Die Thickness	9.1 MILS
Base Bonding Pad Area	7.9 x 7.9 MILS
Emitter Bonding Pad Area	7.9 x 7.9 MILS
Top Side Metalization	Al-Si - 30,000Å
Back Side Metalization	Au-As - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 5 INCH WAFER

11,055

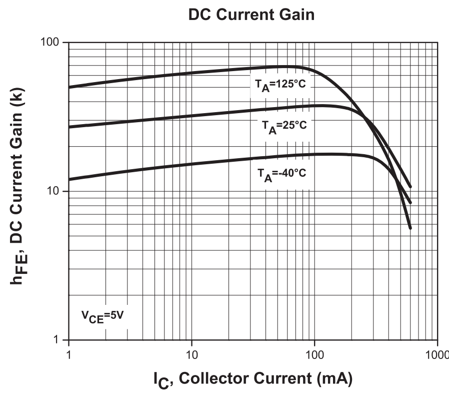
PRINCIPAL DEVICE TYPE

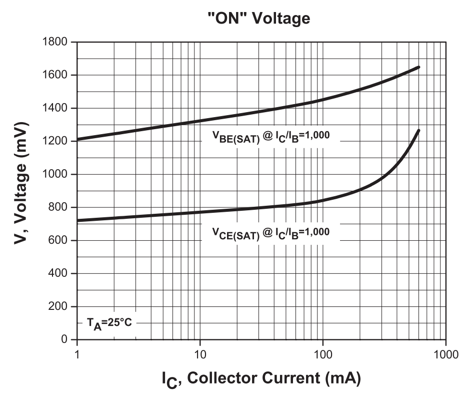
CZT2000

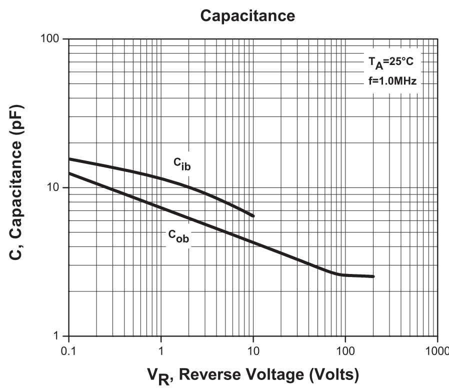
R0 (19-September 2011)

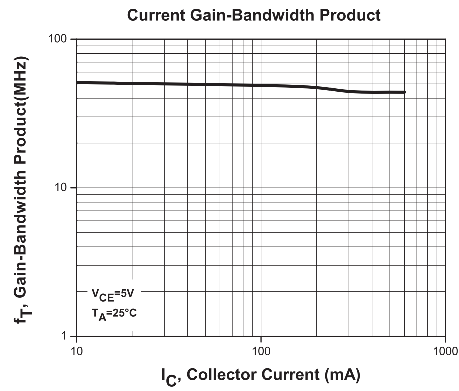
PROCESS CP331

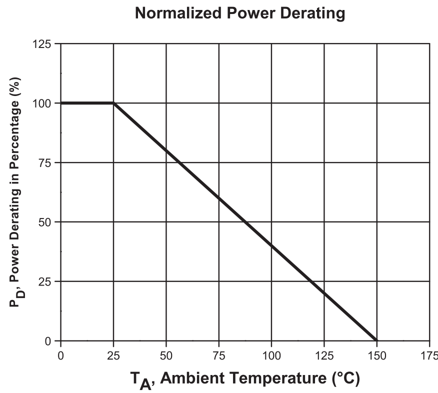
Typical Electrical Characteristics











R0 (19-September 2011)